

## **Treasure Chest** Examples of available chips and structures

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Chip resp. Structure (Measures rounded)	Туре	View
<b>{100}Si-Chip without Structure</b> (further orientations, sizes, thicknesses and coatings by request)		
$\frac{\text{Square}}{\text{square}} \text{ (sawed along <110>)}$ square 10 mm x 10 mm, 525 µm thick, 2-side polished square 10 mm x 10 mm, 525 µm thick, front polished, back lapped	CQ10-525pp CQ10-525pl	Type CQ10-525pp (left) Type CQ10-525pl (right)
Stripe (long side etched, narrow side sawed) rectangular 4 mm x 20 mm, 525 μm thick, 2-side polished, along <110> rectangular 4 mm x 20 mm, 525 μm thick, 2-side polished, along <100> rectangular 4 mm x 40 mm, 525 μm thick, 2-side polished, along <110> rectangular 4 mm x 40 mm, 525 μm thick, 2-side polished, along <100>	C4:20P-525pp C4:20D-525pp C4:40P-525pp C4:40D-525pp	Type CR4:20P-525pp (top) Type CR4:40P-525pp (bottom)
<b>Concave (Hollow)-Pyramids inside an {100}Si-Chip</b> square pyramid, length of edges 410 μm, depth 290 μm		
$\frac{\text{Single pyramid}}{\text{chip size 3 mm x 3 mm about dodecagonal, thickness 300 } \mu\text{m}$	HP3	
Array of 3 x 3 pyramids chip size 10 mm x 10 mm, thickness 300 μm	HP3x3	Туре НР3 Туре НР3х3

Chip with Deepenings of Increasing Depth (3°-Ramp) {111}Si tilted about 3° around <110> trapezoidal deepening: basis 250 μm, height 150 μm, trapezoidal angle 60° depth increasing from the narrow side (1 μm) up to the basis (8 μm) chip size 10 mm x 10 mm <u>5 Groups of ramps</u> (cross like arranged) each with 5 trapezes	TR3	Group of trapezes	Single-trapeze (ramp)
<ul> <li>Chip with Systems of Rings dry etched, other depths by request system of rings:- circular deepening in the centre, diameter 20 μm - 3 rings (width 15 μm), outer diameter 80, 140, 200 μm chip with 3 x 3 systems of rings (distance 2 mm) inside a centre of crosses chip size 10 mm x 10 mm System with depths 100, 200, 300, 400 nm from the centre up to the outside System with depths 400, 300, 200, 100 nm from the centre up to the outside System with depths 300, 100, 200, 400 nm from the centre up to the outside System with depths 200, 400, 100, 300 nm from the centre up to the outside</li> </ul>	RS100:400 RS400:100 RS300:400 RS200:300	Image: Second	System of rings
Chip with a Deepening (Membrane) depth 350 μm, thickness of the membrane 50 μm (others by request) membrane 6 mm x 6 mm (corners blunted) boss: stump of an 8-angular pyramid, top 1 mm x 1 mm chip size 10 mm x 10 mmMembrane without boss Membrane with boss in the centre	M10-50 MB10-50	Туре М 10-50	Туре MB 10-50
Chip with Structured Membrane depth 350 μm, thickness of the membrane 50 μm (others by request) boss: stump of a pyramid chip size 10 mm x 10 mm Stripe-membrane (bridge) along <100>, width 2 mm, without boss along <100>, width 2 mm, with boss (2 mm x 1 mm)	BD10-50 BDB10-50	Type BD10-50	Type BDB10-50

3 Stripe-membranes (bridges) along <110> without boss, width 1, 2, 1 mm along <110> with boss, width 1, 2, 1 mm	3BP10-50 3BPB10-50	Type BP10-50	Type BPB10-50
Crosslike-membrane along <100> with a central boss (1 mm x 1 mm), width 1 mm	KFDB10-50	Type KFDB 10-50	
Chip with Cantilever cantilever thickness 50 μm (others by request) <u>3 Cantilevers along &lt;100&gt;</u> , width 1 mm, length 1, 1, 3 mm, boss 1 mm x 1 mm <u>3 Cantilevers along &lt;110&gt;</u> , width 1, 3, 1 mm,length 6 mm, boss 1(3)mm x 3 mm <u>4 Cantilevers along &lt;110&gt;</u> , width 1 mm, length 1 mm, boss 2 mm x 1 mm chip size 10 mm x 10 mm	3CD-50 3CP-50 4CP-50	Type 3CD-50	P-50
<u>1 Cantilever along &lt;110&gt;</u> , width 1.5 mm, length 8 mm, with boss 1 x 1 mm chip size 5 mm x 15 mm frame with scale	1CP-50	Type 1CP-50 front side	back side
Chip with Torsional Plate (Mirror) plate 4 mm x 6 mm, thickness 50 µm frame for stiffening at the back side no metallization torsional beams at the broadside of the plate: thickness 50 µm, length 1 mm width 0.1 mm chip size 10 mm x 10 mm	TS10-50	Type TS10-50 front side	Dack side

Parallel springs (in plane-bending)size 20 mm x 16 mmsprings: width 525 μm (thickness of the chip), length about 9 mmmounting bar 5 mm x 16 mmcoupling bar 3 mm x 16 mmthickness of springs 50 μm2x1-Spring system2x2-Spring system2x3-Spring system	PSS1 PSS2 PSS3	9 mm       Type PSS3
Straight guide (horizontal) (solid hinges: in plane-bending) stage about 4 mm x 4 mm, travel up to +/-1 mm, load max. 0.1 N chip size 30 mm x 40 mm, thickness 1.2 mm	SGH1	Type SGH1
Hall-Structure electrical resistivity 0.1 Ohmcm stripe: width 2 mm, thickness 50 μm bosses for electrical contacts (without metallisation) for current, potential and Hallvoltage chip size 5 mm x 20 mm	HE-50	Type HE-50 front side
Chip with Edgesheight of edges 350 μmtrapezoidal cross section (narrow side 10 μm)thickness of the membrane 50 μm (others by request)2 Edges, short (4 mm, distance 10 mm)chip size 5 mm x 15 mm1 Edge, long (8 mm)chip size 5 mm x 10 mm	E10-350 2E10-350	Type 2E10-350         Type E10-350